

Edge-TCT studies of irradiated HVCMOS sensor (an update)

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A HVCMOS sensor (HVCMOS2FEI4) was investigated before and after the irradiation with Edge-TCT. Key properties of the charge collection in p substrate were determined by different analysis methods. It was found that diffusion contribution to the the charge collection is reduced, but the depleted region is not affected much after relatively low fluences of up to 5×10^{14} neq/cm².

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